# UTC UNISONIC TECHNOLOGIES CO., LTD

# 8050S

### NPN SILICON TRANSISTOR

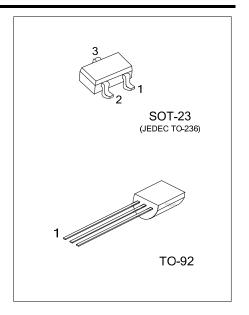
# **LOW VOLTAGE HIGH CURRENT SMALL SIGNAL** NPN TRANSISTOR

#### DESCRIPTION

The UTC 8050S is a low voltage high current small signal NPN transistor, designed for Class B push-pull audio amplifier and general purpose applications.

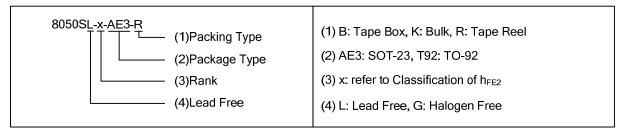
#### **FEATURES**

- \*Collector current up to 700mA
- \*Collector-Emitter voltage up to 20V
- \*Complementary to UTC 8550S

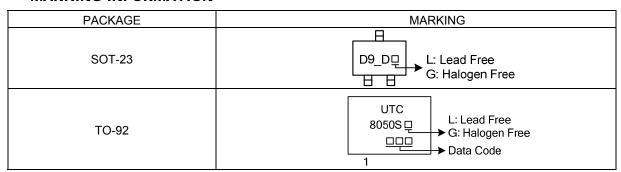


#### ORDERING INFORMATION

Ordering	Dookogo	Pin Assignment			Dealine	
Lead Free	Halogen-Free	Package	1	2	3	Packing
8050SL-x-AE3-R	8050SG-x-AE3-R	SOT-23	Е	В	С	Tape Reel
8050SL-x-T92-B	8050SG-x-T92-B	TO-92	Е	С	В	Tape Box
8050SL-x-T92-K	8050SG-x-T92-K	TO-92	Е	С	В	Bulk



#### MARKING INFORMATION



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## ■ ABSOLUTE MAXIMUM RATING (T<sub>A</sub>=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Base Voltage		$V_{CBO}$	30	V
Collector-Emitter Voltage		$V_{CEO}$	20	V
Emitter-Base Voltage		$V_{EBO}$	5	V
Collector Current		Ic	700	mA
O-Ht Diiti(T. 05°C)	SOT-23		350	mW
Collector Dissipation(T <sub>A</sub> =25°C)	TO-92	Pc	1	W
Junction Temperature		TJ	+150	°C
Storage Temperature		T <sub>STG</sub>	-40 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

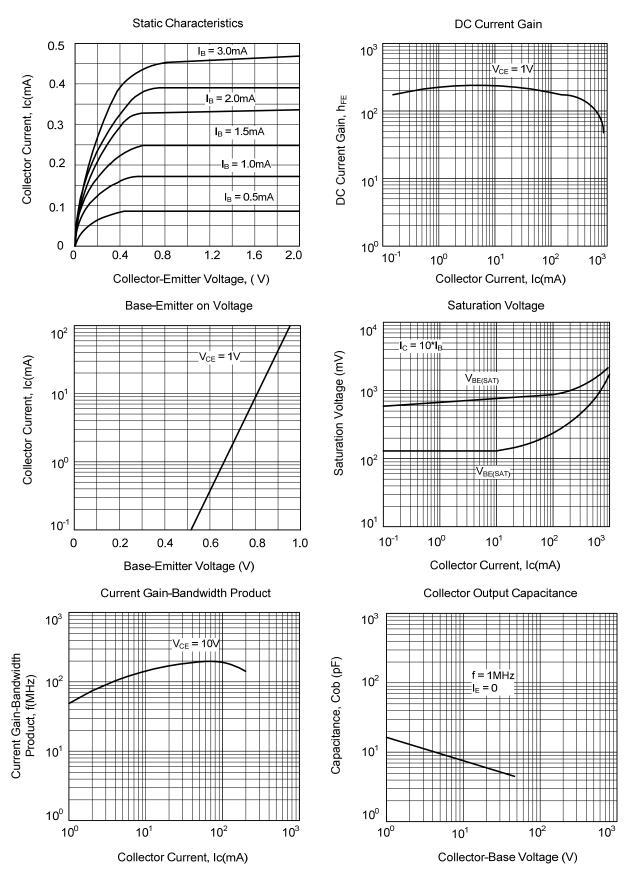
## ■ ELECTRICAL CHARACTERISTICS (T<sub>A</sub>=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	$BV_{CBO}$	$I_{\rm C} = 100 \mu A, I_{\rm E} = 0$	30			V
Collector-Emitter Breakdown Voltage	$BV_CEO$	$I_{\rm C} = 1 {\rm mA}, I_{\rm B} = 0$	20			V
Emitter-Base Breakdown Voltage	$BV_{EBO}$	$I_E = 100 \mu A, I_C = 0$	5			V
Collector Cut-Off Current	I <sub>CBO</sub>	$V_{CB} = 30V, I_{E} = 0$			1	uA
Emitter Cut-Off Current	I <sub>EBO</sub>	$V_{EB} = 5V, I_{C} = 0$			100	nA
	h <sub>FE1</sub>	$V_{CE} = 1V, I_C = 1mA$	100			
DC Current Gain (note)	h <sub>FE2</sub>	$V_{CE} = 1V, I_{C} = 150 \text{ mA}$	120		400	
	h <sub>FE3</sub>	$V_{CE} = 1V, I_{C} = 500mA$	40			
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	$I_C = 500 \text{mA}, I_B = 50 \text{mA}$			0.5	V
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	$I_C = 500 \text{mA}, I_B = 50 \text{mA}$			1.2	V
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	$V_{CE}$ = 1V, $I_C$ = 10mA			1.0	V
Current Gain Bandwidth Product	f <sub>T</sub>	$V_{CE} = 10V, I_{C} = 50mA$	100			MHz
Output Capacitance	Cob	$V_{CB} = 10V, I_E = 0, f = 1MHz$		9.0		pF

# ■ CLASSIFICATION OF h<sub>FE2</sub>

RANK	С	D	Е	
RANGE	120-200	160-300	280-400	

#### TYPICAL CHARACTERISTICS



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